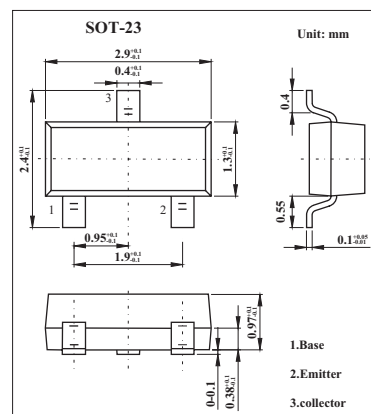


NPN Silicon Transistor

2SC5343SF

■ Features

- Low collector saturation voltage: $V_{CE}=0.25V(\text{Max.})$
- Low output capacitance: $C_{ob}=2pF(\text{Typ.})$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=10\mu A, I_C=0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current transfer ratio	h_{FE}	$V_{CE}=6V, I_C=2mA$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C/I_B=100mA/10mA$			0.25	V
Transition frequency	f_T	$V_{CE}=10V, I_C=1mA,$	80			MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		2	3.5	pF
Noise figure	NF	$V_{CE}=6V, I_C=0.1mA, f=1KHz, R_g=10k\Omega$			10	dB

■ h_{FE} Classification

Marking	DA			
Rank	O	Y	G	L
h_{FE}	70~140	120~240	200~400	300~700